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Doc No. TT4-EA-10241

Revision. 2

# **Panasonic**

MOS FET MTM982400BBF

Unit: mm

## MTM982400BBF

#### Silicon N-channel MOSFET

#### For switching

#### ■ Features

- Low drain-source On-state Resistance RDS(on) typ =  $29 \text{ m}\Omega$  (VGS = 5.0 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: CA

#### ■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

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5. Drain

0.95

2. Source3. Source6. Drain7. Drain

5.0

LJ1 LJ2 LJ3 LJ4

1. 27

1. Source

4. Gate

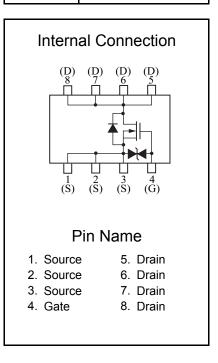
7. Drain8. Drain

Panasonic	SO8-F1-B
JEITA	SC-111AA
Code	_

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	40	V
Gate-source Voltage	VGS	±20	V
Drain Current	ID	7	Α
Drain Current (Pulsed)	IDp	28	Α
Total Power dissipation *1	PD	2	W
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note: \*1 Measuring on ceramic board at 50 mm  $\times$  50 mm  $\times$  1.0 mm.



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MOS FET MTM982400BBF

#### ■ Electrical Characteristics Ta = 25°C ± 3°C Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	40			V
Zero Gate Voltage Drain Current	IDSS	VDS = 40 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μΑ
Gate-source threshold Voltage	Vth	ID = 1.0 mA, VDS = 10.0 V	1.0		2.5	V
Drain-source On-state Resistance *1	RDS(on)1	ID = 7 A, VGS = 10 V		16	23	mΩ
	RDS(on)2	ID = 3.5 A, VGS = 5.0 V		29	40	
Forward transfer admittance *1	Yfs	ID = 7 A, VDS = 10 V	4.0			S
Input Capacitance	Ciss			1 750		
Output Capacitance	Coss	VDS = 10 V, VGS = 0 V, f = 1 MHz		150		pF
Reverse Transfer Capacitance	Crss			90		
Turn-on Delay Time *1,*2	td(on)	VDD = 25 V, VGS = 0 to 10 V,		17		no
Rise Time *1,*2	tr	ID = 3.5 A		9		ns
Turn-off Delay Time *1,*2	td(off)	VDD = 25 V, VGS = 10 to 0 V,		94		ns
Fall Time *1,*2	tf	ID = 3.5 A		33		

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

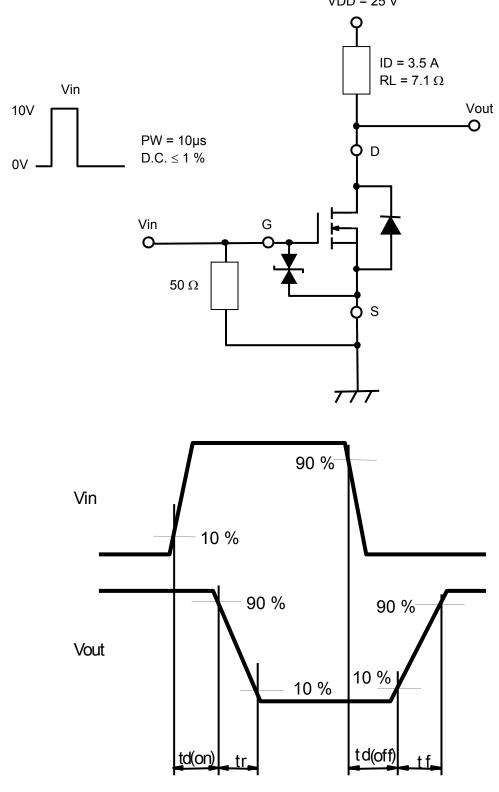
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Established: 2007-12-18 : 2013-09-10 Revised

<sup>2. \*1</sup> Pulse test

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time **VDD = 25 V** 

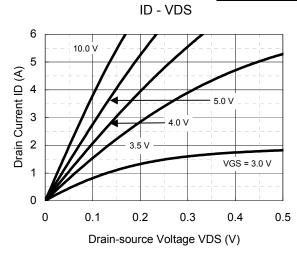


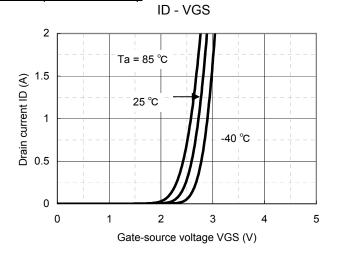
Established: 2007-12-18 : 2013-09-10 Revised

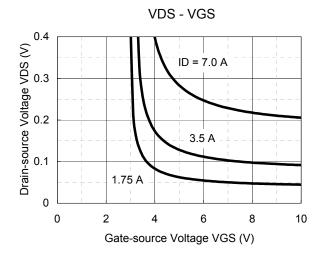
**Panasonic** 

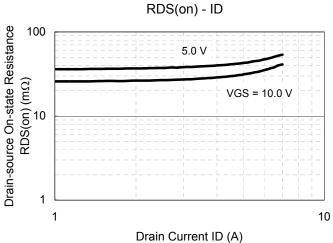
MOS FET MTM982400BBF

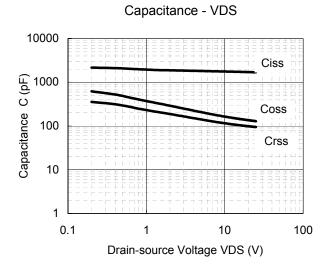
## Technical Data (reference)

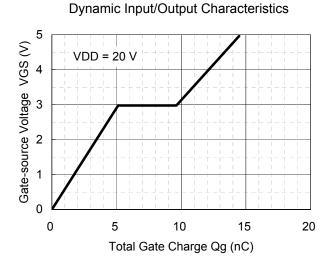








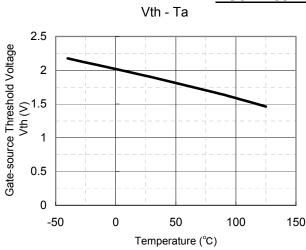


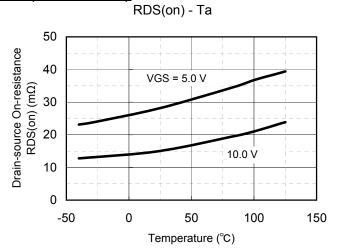


# **Panasonic**

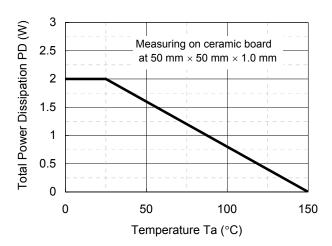
# MOS FET MTM982400BBF

## Technical Data (reference)

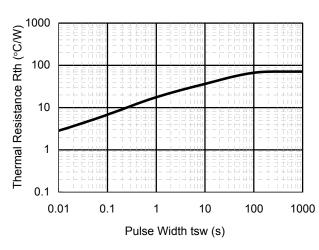


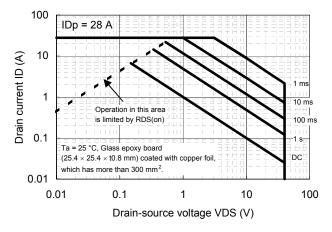


PD - Ta



Rth - tsw Safe Operating Area



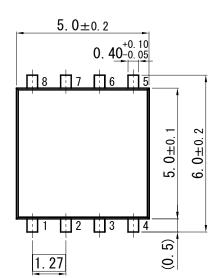


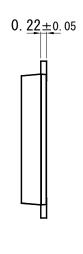
MOS FET MTM982400BBF

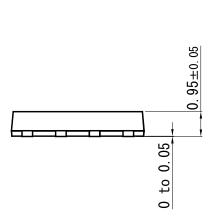
Unit: mm

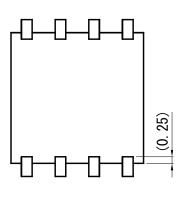
# **Panasonic**

SO8-F1-B

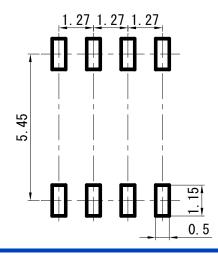








Land Pattern (Reference) (Unit : mm)



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